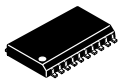
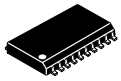
3-STATE Octal D-Type Latch

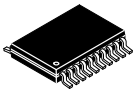
MM74HC373



SOIC−20 WB
CASE 751D−05



SOIC−20, 300 mils
CASE 751BJ−01



TSSOP−20 WB
CASE 948E

General Description

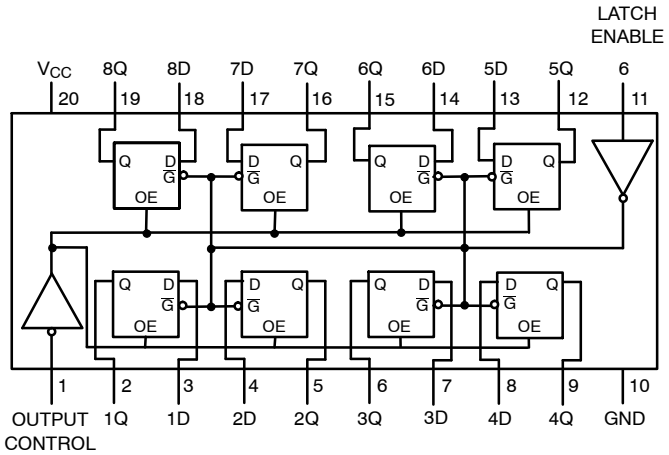
The MM74HC373 high speed octal D−type latches utilize advanced silicon−gate CMOS technology. They possess the high noise immunity and low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LS−TTL loads. Due to the large output drive capability and the 3−STATE feature, these devices are ideally suited for interfacing with bus lines in a bus organized system.

When the LATCH ENABLE input is HIGH, the Q outputs will follow the D inputs. When the LATCH ENABLE goes LOW, data at the D inputs will be retained at the outputs until LATCH ENABLE returns HIGH again. When a high logic level is applied to the OUTPUT CONTROL input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

The 74HC logic family is speed, function, and pin−out compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical Propagation Delay: 18 ns
- Wide Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA Maximum
- Low Quiescent Current: 160 μA Maximum (74 Series)
- Output Drive Capability: 15 LS−TTL Loads
- This is a Pb−Free Device

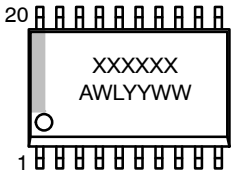


Pin Assignments for SOIC and TSSOP (Top View)

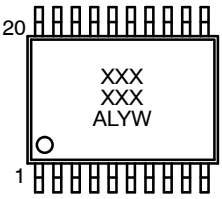
Figure 1. Connection Diagram

MARKING DIAGRAMS

SOIC−20



TSSOP−20



XXXXXX	=	Specific Device Code
A	=	Assembly Location
WL, L	=	Wafer Lot Number
Y	=	Year
WW, YW	=	Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

TRUTH TABLE

Output Control	Latch Enable	Data	373 Output
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

NOTES:
H = HIGH Level
L = LOW Level
X = Don't Care
Q_0 = Level of output before steady−state input conditions were established.
Z = High Impedance

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Rating		Value	Unit
V_{CC}	Supply Voltage		−0.5 to +6.5 V	V
V_{IN}	DC Input Voltage		−0.5 to V_{CC} +0.5 V	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} +0.5 V	V
I_{IK}, I_{OK}	Clamp Diode Current		±20	mA
I_{OUT}	DC Output Current, per pin		±35	mA
I_{CC}	DC V_{CC} or GND Current, per pin		±70	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
P_D	Power Dissipation	SOIC	1302	mW
		TSSOP	833	mW
T_L	Lead Temperature (Soldering 10 seconds)		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Unless otherwise specified all voltages are referenced to ground.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage		2	6	V
V_{IN}, V_{OUT}	DC Input or Output Voltage		0	V_{CC}	V
T_A	Operating Temperature Range		−55	+125	°C
t_r, t_f	Input Rise or Fall Times	V_{CC} = 2.0 V	−	1000	ns
		V_{CC} = 4.5 V	−	500	ns
		V_{CC} = 6.0 V	−	400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Note 2)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C	Unit
				Typ	Guaranteed Limits		
V_{IH}	Minimum HIGH Level Input Voltage		2.0 V 4.5 V 6.0 V		1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V V V
V_{IL}	Maximum LOW Level Input Voltage		2.0 V 4.5 V 6.0 V		0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V V V
V_{OH}	Minimum HIGH Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $\|I_{OUT}\| \le 20$ μA	2.0 V 4.5 V 6.0 V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V V V
		$V_{IN} = V_{IH}$ or V_{IL} $\|I_{OUT}\| \le 6.0$ mA $\|I_{OUT}\| \le 7.8$ mA	 4.5 V 6.0 V	 4.2 5.7	 3.98 5.48	 3.84 5.34	 3.7 5.2	 V V
V_{OL}	Maximum LOW Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $\|I_{OUT}\| \le 20$ μA	2.0 V 4.5 V 6.0 V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V V
		$V_{IN} = V_{IH}$ or V_{IL} $\|I_{OUT}\| \le 6.0$ mA $\|I_{OUT}\| \le 7.8$ mA	 4.5 V 6.0 V	 0.2 0.2	 0.26 0.26	 0.33 0.33	 0.4 0.4	 V V
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0 V		±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum 3−STATE Output Leakage Current	$V_{IN} = V_{IH}$ or V_{IL}, OC = V_{IH} $V_{OUT} = V_{CC}$ or GND	6.0 V		±0.5	±5	±10	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND I_{OUT} = 0 μA	6.0 V		8.0	80	160	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. For a power supply of 5 V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5 V. Thus the 4.5 V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5 V and 4.5 V respectively. (The V_{IH} value at 5.5 V is 3.85 V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0 V values should be used.

AC ELECTRICAL CHARACTERISTICS

(V_{CC} = 5 V, T_A = 25°C, $t_r = t_f$ = 6 ns)

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Unit
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to Q	C_L = 45 pF	18	25	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, LE toQ	C_L = 45 pF	21	30	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time	R_L = 1 kΩ, C_L = 45 pF	20	28	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time	R_L = 1 kΩ, C_L = 5 pF	18	25	ns
t_s	Minimum Set Up Time			5	ns
t_H	Minimum Hold Time			10	ns
t_W	Minimum Pulse Width		9	16	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

(V_{CC} = 2.0–6.0 V, C_L = 50 pF, $t_r = t_f$ = 6 ns, unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	T_A = −40 to 85°C	T_A = −55 to 125°C		Unit
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Data to Q	C_L = 50 pF	2.0 V	50	150	188	225	ns
		C_L = 150 pF	2.0 V	80	200	250	300	ns
		C_L = 50 pF	4.5 V	22	30	37	45	ns
		C_L = 150 pF	4.5 V	30	40	50	60	ns
		C_L = 50 pF	6.0 V	19	26	31	39	ns
		C_L = 150 pF	6.0 V	26	35	44	53	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, LE to Q	C_L = 50 pF	2.0 V	63	175	220	263	ns
		C_L = 150 pF	2.0 V	110	225	280	338	ns
		C_L = 50 pF	4.5 V	25	35	44	52	ns
		C_L = 150 pF	4.5 V	35	45	56	68	ns
		C_L = 50 pF	6.0 V	21	30	37	45	ns
		C_L = 150 pF	6.0 V	28	39	49	59	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time	R_L = 1 kΩ						
		C_L = 50 pF	2.0 V	50	150	188	225	ns
		C_L = 150 pF	2.0 V	80	200	250	300	ns
		C_L = 50 pF	4.5 V	21	30	37	45	ns
		C_L = 150 pF	4.5 V	30	40	50	60	ns
		C_L = 50 pF	6.0 V	19	26	31	39	ns
		C_L = 150 pF	6.0 V	26	35	44	53	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time	R_L = 1 kΩ	2.0 V	50	150	188	225	ns
		C_L = 50 pF	4.5 V	21	30	37	45	ns
			6.0 V	19	26	31	39	ns
t_s	Minimum Set Up Time		2.0 V	–	50	60	75	ns
			4.5 V	–	9	13	15	ns
			6.0 V	–	9	11	13	ns
t_H	Minimum Hold Time		2.0 V	–	5	5	5	ns
			4.5 V	–	5	5	5	ns
			6.0 V	–	5	5	5	ns
t_W	Minimum Pulse Width		2.0 V	30	80	100	120	ns
			4.5 V	10	16	20	24	ns
			6.0 V	9	14	18	20	ns
t_{THL}, t_{TLH}	Maximum Output Rise and Fall Time	C_L = 50 pF	2.0 V	25	60	75	90	ns
			4.5 V	7	12	15	18	ns
			6.0 V	6	10	13	15	ns
C_{PD}	Power Dissipation Capacitance (Note 3)	(per latch)						
		OC = V_{CC}	–	30	–	–	–	pF
		OC = GND	–	50	–	–	–	pF
C_{IN}	Maximum Input Capacitance		–	5	10	10	10	pF
C_{OUT}	Maximum Output Capacitance		–	15	20	20	20	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

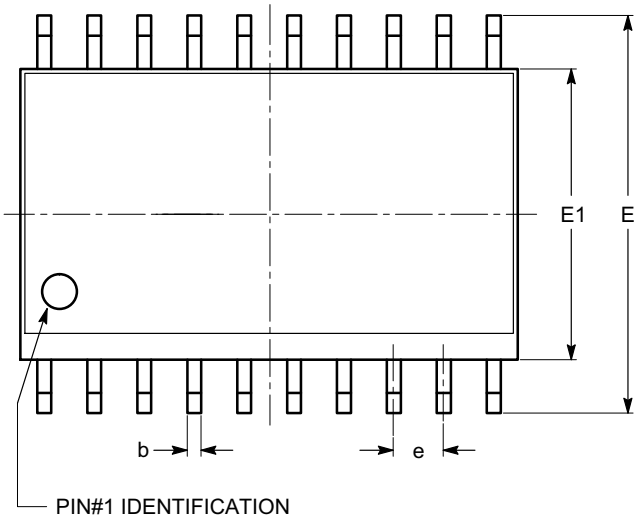
ORDERING INFORMATION

Device	Marking	Package	Shipping†
MM74HC373WM	HC373A	SOIC−20 WB (Pb−Free and Halide Free)	38 Units / Tube
MM74HC373WMX	HC373A	SOIC−20, 300 mils (Pb−Free and Halide Free)	1000 / Tape & Reel
MM74HC373MTC	HC 373A	TSSOP−20 WB (Pb−Free)	75 Units / Tube
MM74HC373MTCX	HC 373A	TSSOP−20 WB (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

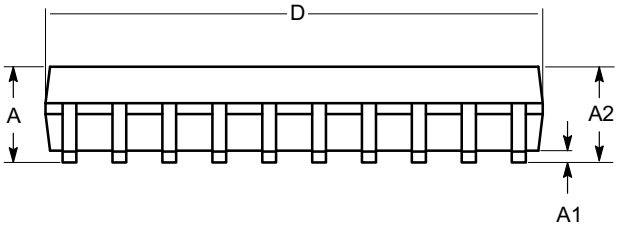
SOIC−20, 300 mils
CASE 751BJ
ISSUE O

DATE 19 DEC 2008

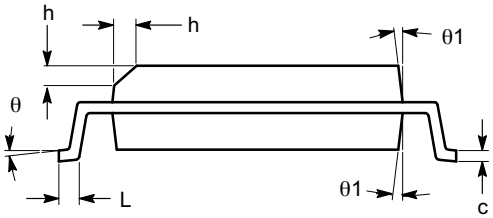


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	2.36	2.49	2.64
A1	0.10		0.30
A2	2.05		2.55
b	0.31	0.41	0.51
c	0.20	0.27	0.33
D	12.60	12.80	13.00
E	10.01	10.30	10.64
E1	7.40	7.50	7.60
e		1.27 BSC	
h	0.25		0.75
L	0.40	0.81	1.27
θ	0°		8°
θ1	5°		15°



SIDE VIEW



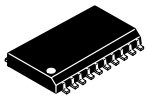
END VIEW

Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MS-013.

DOCUMENT NUMBER:	98AON34287E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC−20, 300 MILS	PAGE 1 OF 1

SOIC−20 WB
CASE 751D−05
ISSUE H

DATE 22 APR 2015



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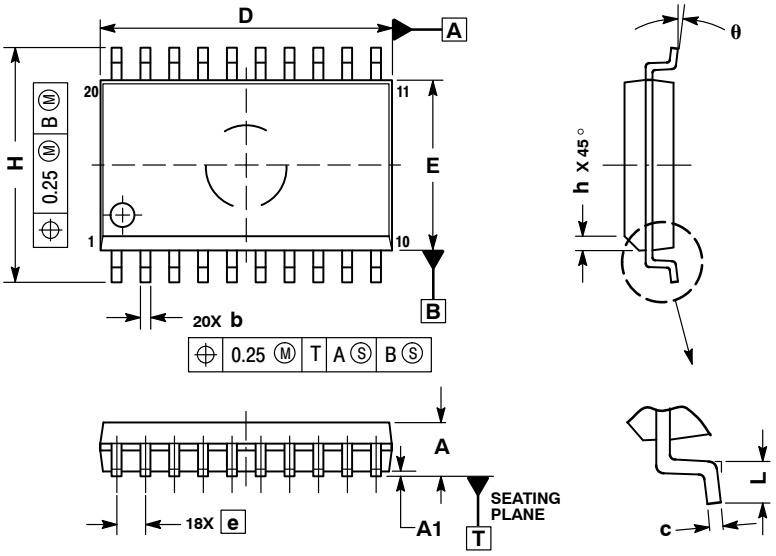
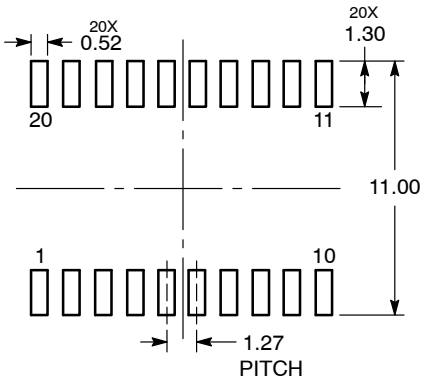


NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

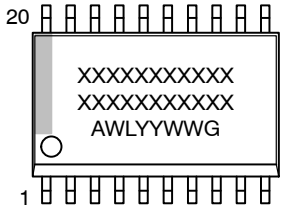
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



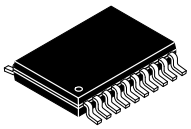
XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98ASB42343B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOIC−20 WB**		**PAGE 1 OF 1**

TSSOP–20 WB
CASE 948E
ISSUE D

DATE 17 FEB 2016



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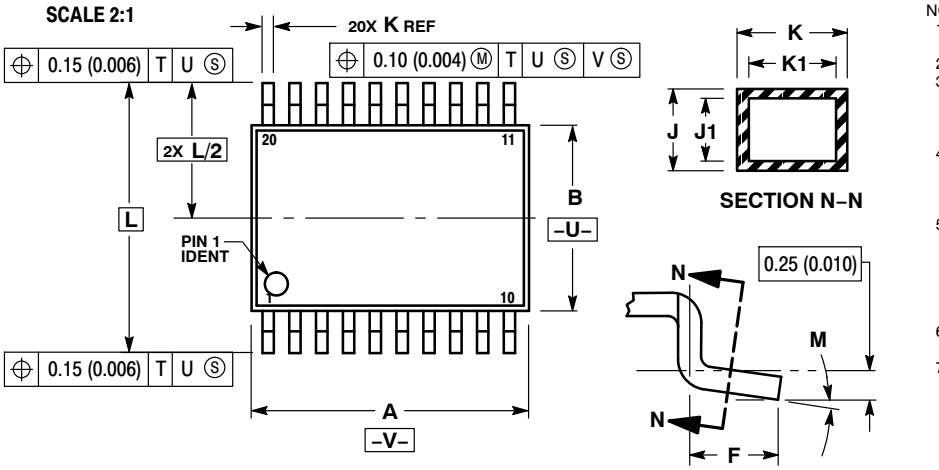
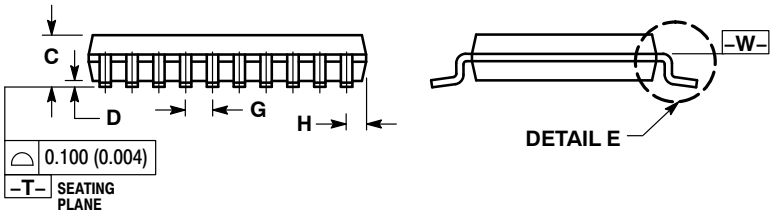


SECTION N–N

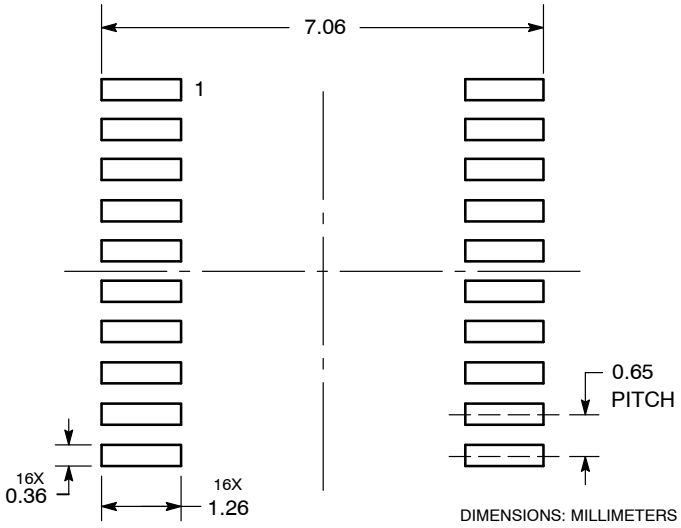
DETAIL E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

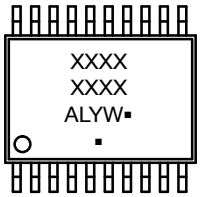
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98ASH70169A**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**TSSOP–20 WB**		**PAGE 1 OF 1**

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